

High Speed Infrared Emitting Diode, 940 nm, GaAlAs Double Hetero



21531

DESCRIPTION

VSMB1940X01 is an infrared, 940 nm emitting diode in GaAlAs Double Hetero technology with high radiant power and high speed, molded in clear, untinted 0805 plastic package for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- AEC-Q101 qualified
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- High speed
- Angle of half sensitivity: $\phi = \pm 60^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- 0805 standard surface-mountable package
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



APPLICATIONS

- High speed IR data transmission
- High power emitter for low space applications
- High performance transmissive or reflective sensors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMB1940X01	6	± 60	940	15

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMB1940X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.1, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	1	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	270	K/W

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

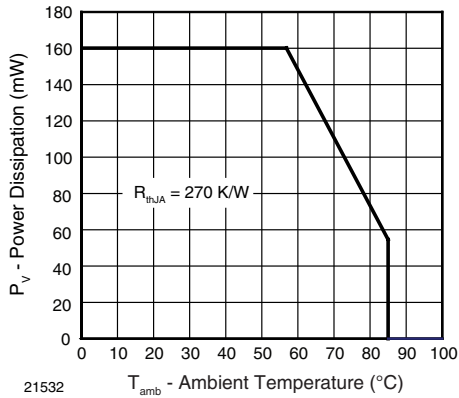


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

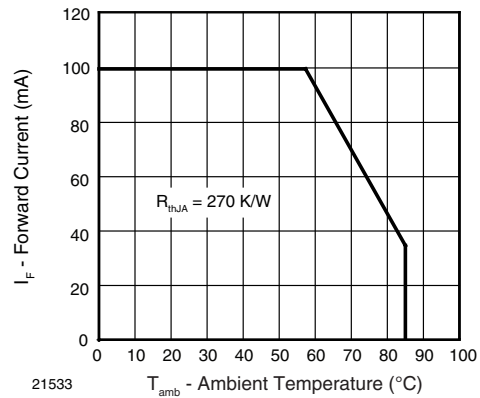


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F	1.15	1.35	1.6	V
	I _F = 1 A, t _p = 100 μs	V _F		2.2		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{V_F}		- 1.5		mV/K
	I _F = 100 mA	TK _{V_F}		- 1.1		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0 mW/cm ²	C _J		70		pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	I _e	3	6	12	mW/sr
	I _F = 1 A, t _p = 100 μs	I _e		60		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		40		mW
Temperature coefficient of radiant power	I _F = 1 mA	TK _{φ_e}		- 1.1		%/K
	I _F = 100 mA	TK _{φ_e}		- 0.51		%/K
Angle of half intensity		φ		± 60		deg
Peak wavelength	I _F = 30 mA	λ _p		940		nm
Spectral bandwidth	I _F = 30 mA	Δλ		25		nm
Temperature coefficient of λ _p	I _F = 30 mA	TK _{λ_p}		0.25		nm
Rise time	I _F = 100 mA, 20 % to 80 %	t _r		15		ns
Fall time	I _F = 100 mA, 20 % to 80 %	t _f		15		ns
Virtual source diameter		d		0.5		mm

Note

T_{amb} = 25 °C, unless otherwise specified

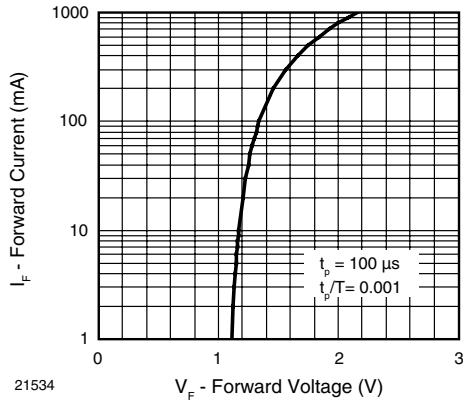
BASIC CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified


Fig. 3 - Forward Current vs. Forward Voltage

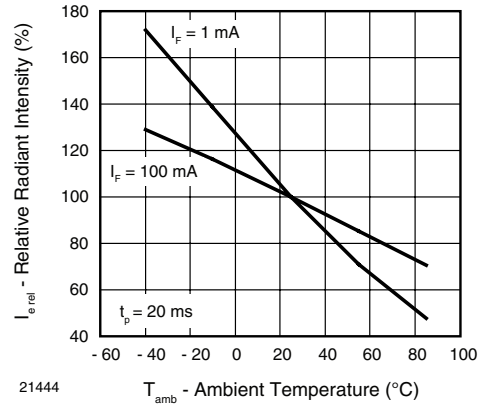


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

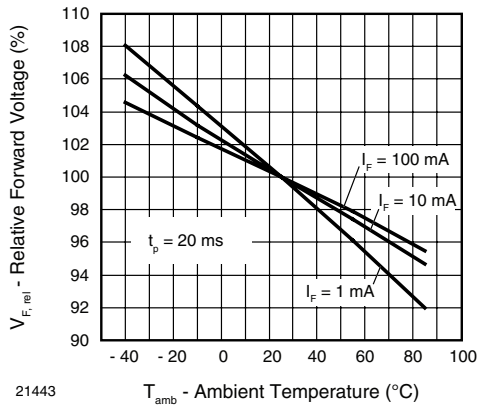


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

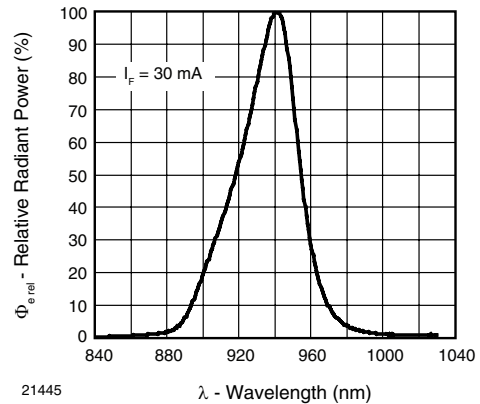


Fig. 7 - Relative Radiant Power vs. Wavelength

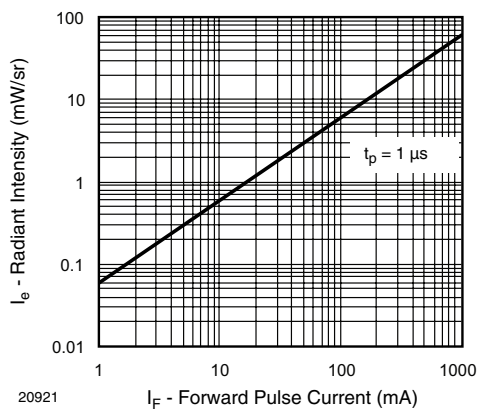


Fig. 5 - Radiant Intensity vs. Forward Current

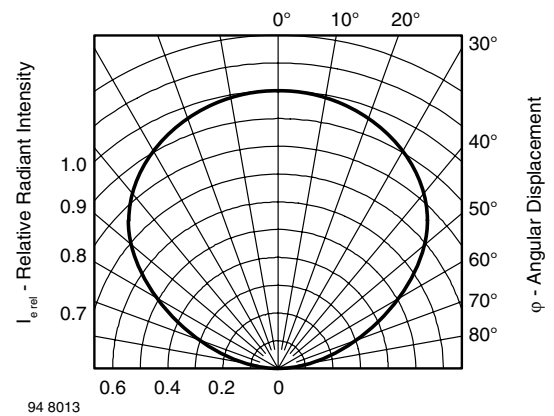


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

REFLOW SOLDER PROFILE

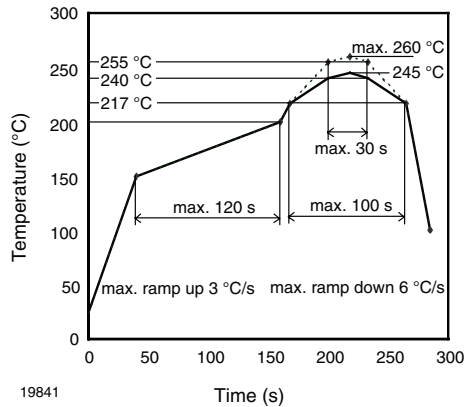


Fig. 9 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

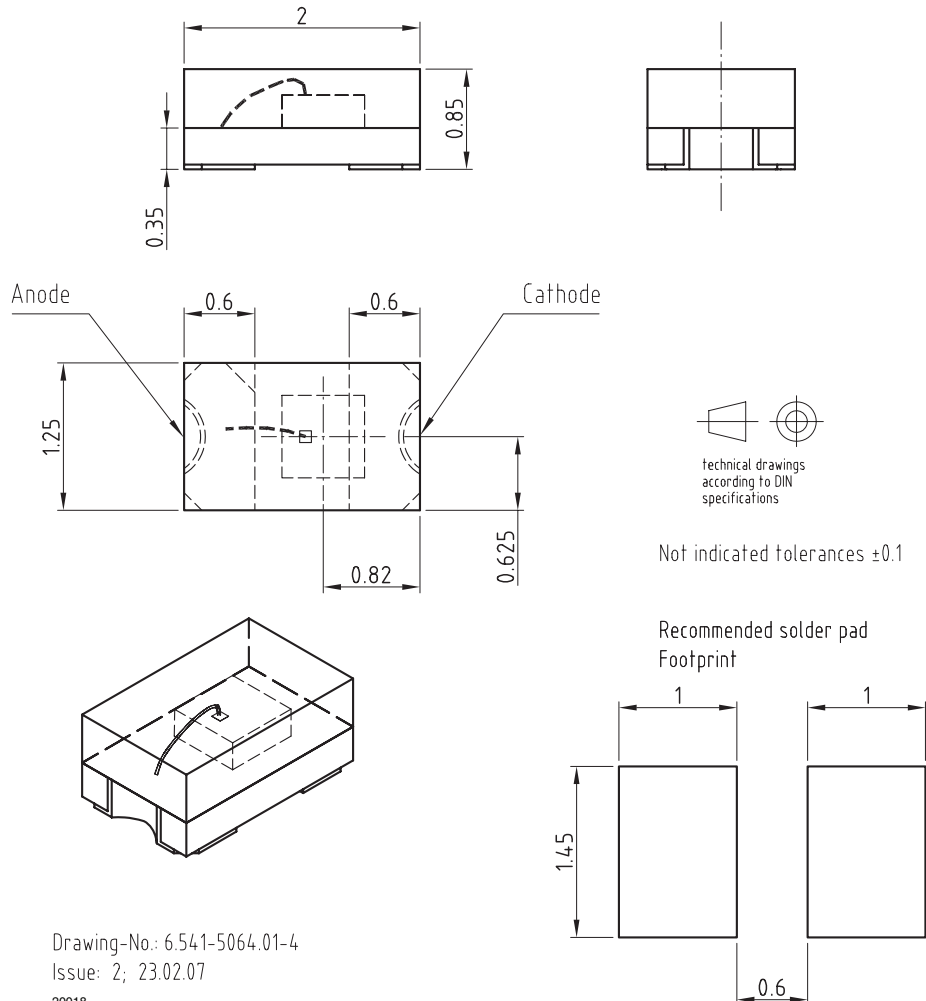
Floor life: 168 h

Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, $\text{RH} < 60\%$

DRYING

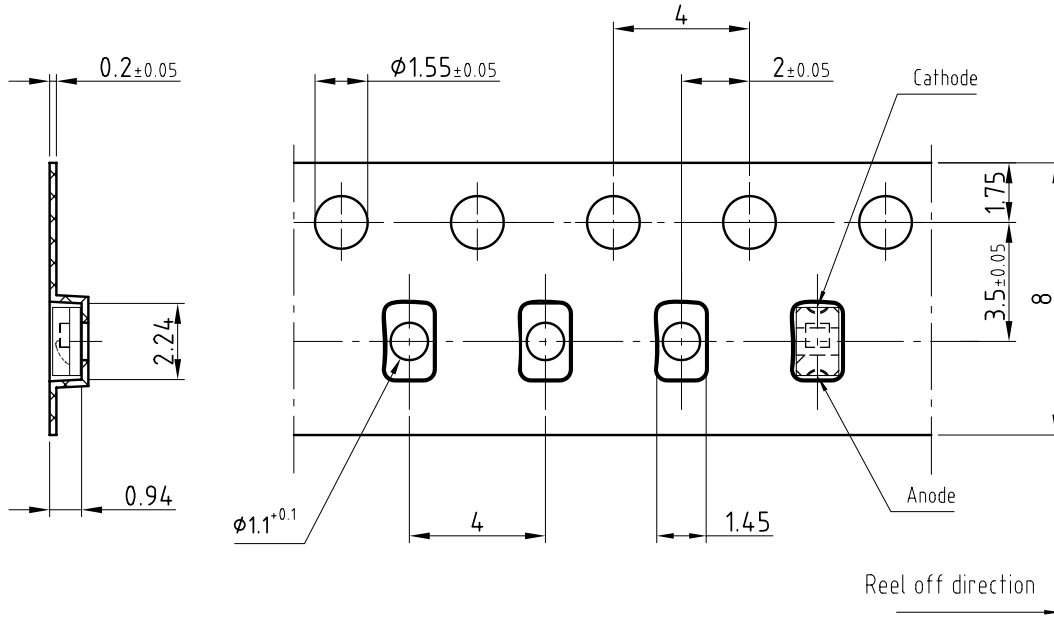
In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ }^{\circ}\text{C}$ (+ $5\text{ }^{\circ}\text{C}$), $\text{RH} < 5\%$.

PACKAGE DIMENSIONS in millimeters





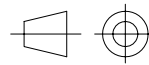
BLISTER TAPE DIMENSIONS in millimeters



Drawing-No.: 9.700-5311.01-4

Issue: 1; 23.02.07

21501



technical drawings
according to DIN
specifications

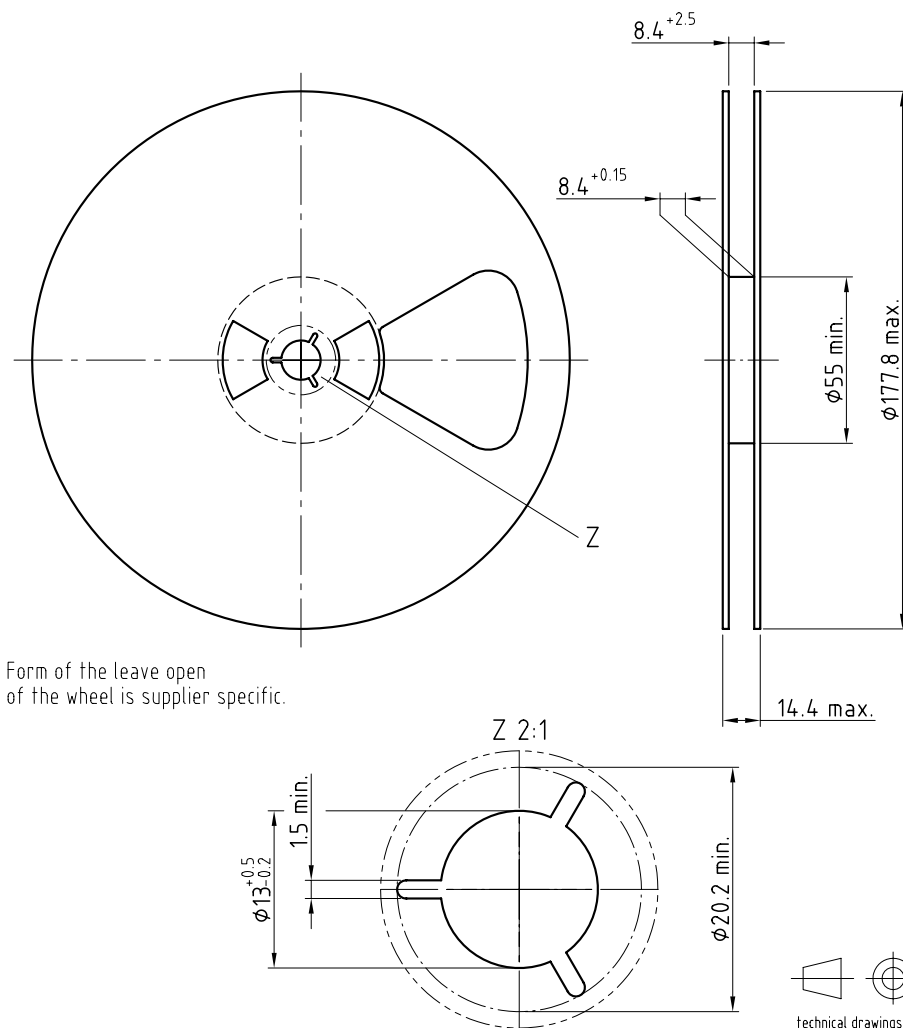
Not indicated tolerances ± 0.1

VSMB1940X01



Vishay Semiconductors High Speed Infrared Emitting Diode,
940 nm, GaAlAs Double Hetero

REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5096.01-4

Issue: 1; 05.05.08

20875



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